

TOSHIBA LED LAMP InGaAlP ORANGE LIGHT EMISSION

TLOH262

PANEL CIRCUIT INDICATOR

- 3.1mm DIAMETER (T1)
- InGaAlP ORANGE LED
- All Plastic Mold Type.
- Colorless Clear Lens
- Low Drive Current, High Intensity Orange Light Emission
Recommended Forward Current : $I_F=1\sim 20\text{mA}$ (DC)
- All Plastic Molded Lens, Provides an Excellent ON-OFF Contrast Ratio.
- Fast Response Time, Capable of Pulse Operation.
- High Power Luminous Intensity
- APPLICATIONS : Suitable for Backlighting.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current (DC)	I_F	50	mA
Reverse Voltage	V_R	4	V
Power Dissipation	P_D	125	mW
Operating Temperature Range	T_{opr}	-30~85	°C
Storage Temperature Range	T_{stg}	-40~120	°C

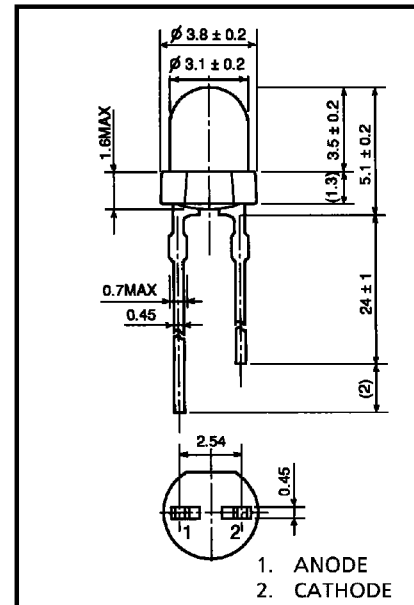
ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F=20\text{mA}$	—	2.1	2.5	V
Reverse Current	I_R	$V_R=4\text{V}$	—	—	50	μA
Luminous Intensity	TLOH262	$I_F=20\text{mA}$ (Note)	153	300	—	mcd
	TLOH262 (PQ)		153	—	736	
Peak Emission Wavelength	λ_p	$I_F=20\text{mA}$	—	612	—	nm
Spectral Line Half Width	$\Delta\lambda$	$I_F=20\text{mA}$	—	15	—	nm
Dominant Wavelength	λ_d	$I_F=20\text{mA}$	—	605	—	nm

(Note) Rank selection carried out under next range respectively, although it needs $\pm 15\%$ additional for guaranteed limits.

P : 180-360mcd, Q : 320-640mcd, R : 560-1120mcd.

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	4-3H1

Weight : 0.14g

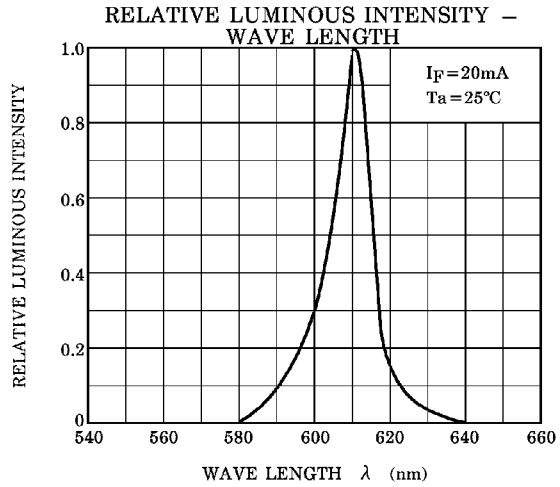
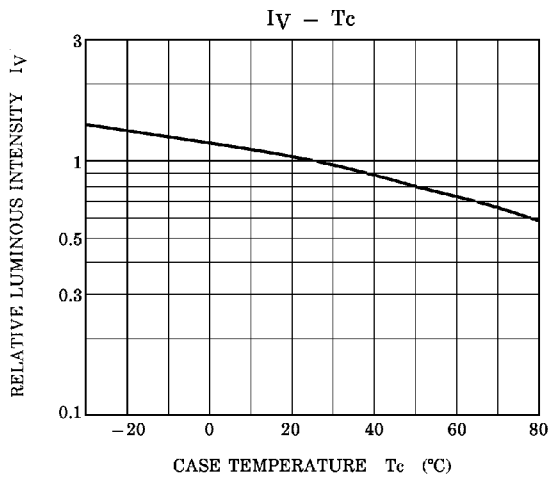
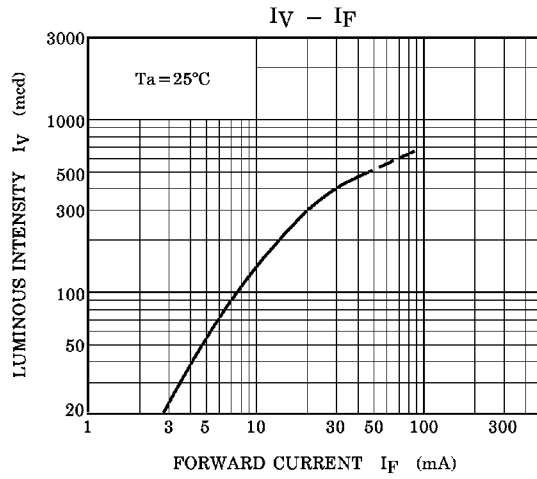
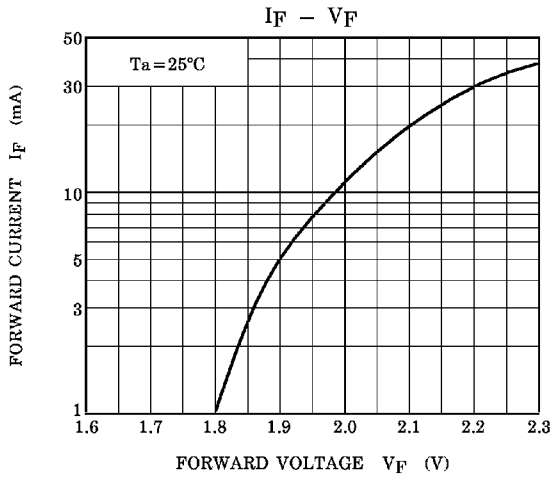
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PRECAUTION

Please be careful of the followings

- Soldering temperature : 260°C MAX. Soldering time : 3s MAX.
(Soldering portion of lead : up to 2mm from the body of the device)
- If the lead is formed, the lead should be formed up to 5mm from the body of the device without forming stress to the resin. Soldering should be performed after lead forming.



RADIATION PATTERN

